

Amendments to the Claims

H¹
Claims 1-59 (Cancelled).

60. (Currently amended) A semiconductor processing method of depositing SiO₂ on a substrate comprising:

providing a substrate within a chemical vapor deposition reactor, the chemical vapor deposition reactor being a cold wall reactor;

feeding a gaseous silicon precursor into the chemical vapor deposition reactor;

feeding gaseous H₂O₂ into the chemical vapor deposition reactor; and

utilizing the silicon precursor, depositing SiO₂ over a surface of the substrate at a rate of about 7000 Å per minute to form a layer of SiO₂.

61. (Previously presented) The semiconductor processing method of claim 60 wherein the gaseous H₂O₂ and the gaseous silicon precursor are fed into the chemical vapor deposition reactor independently.

62. (Previously presented) The semiconductor processing method of claim 60 wherein the gaseous H₂O₂ and the gaseous silicon precursor are fed into the chemical vapor deposition reactor simultaneously.

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63. (Previously presented) The semiconductor processing method of claim 60 wherein the gaseous H_2O_2 and the gaseous silicon precursor are comprised by a gaseous mixture which is fed into the chemical vapor deposition reactor.

64. (Previously presented) The semiconductor processing method of claim 60 further comprising feeding gaseous H_2O into the chemical vapor deposition reactor.

65. (Cancelled).

66. (Previously presented) The semiconductor processing method of claim 60 wherein the surface of the substrate comprises a high aspect ratio topology and wherein the layer is conformally deposited over the topology.

67. (Previously presented) The semiconductor processing method of claim 60, wherein the silicon precursor is selected from the group consisting of: tetraethoxysilane (TEOS), diethylsilane (DES), tetramethylcyclo-tetrasiloxane (TMCTS), fluorotriethoxysilane (FTES), and fluorotrialkoxysilane (FTAS).

68. (Previously presented) The semiconductor processing method of claim 60 wherein the depositing is conducted at a processing temperature of about $400^{\circ}C$.

69. (Cancelled)

H' 70. (Previously presented) The semiconductor processing mixture of claim 63 wherein the gaseous mixture comprises from about 5% to about 15% by volume of H₂O₂.
